

Contents

Acronyms	1
Symbols	4
1 Introduction	7
1.1 The Semiconductor Industry	7
1.2 Dopant Profiling Requirements	10
2 Review of Dopant Profiling Techniques	13
2.1 1D Dopant Profiling Techniques	15
2.1.1 Spreading Resistance Profiling	15
2.1.2 Secondary Ion Mass Spectroscopy	20
2.1.3 Electrochemical C-V Profiling	23
2.2 2D Dopant Mapping Techniques	25
2.2.1 Chemical Staining/Etching	25
2.2.2 Secondary Electron Dopant Contrast	26
2.2.3 Scanning Probe Techniques in General	27
2.2.4 Scanning Capacitance Microscopy	30
2.3 Other Dopant Analysis Techniques	33
3 SSRM Methodology	35
3.1 SSRM as a Secondary AFM Imaging Mode	35
3.1.1 Measurement Setup	37
3.1.2 Nano-Electric Point Contact	40
3.1.3 Back Contact	48
3.1.4 Logarithmic Current Amplifier	51
3.2 Sample Preparation	52
3.2.1 Cleaving	54
3.2.2 Mechanical Grinding and Polishing	56
3.2.3 Focused Ion Beam	59
3.3 Probes	64
3.3.1 Diamond coated Probes	64
3.3.2 Pyramidal moulded Diamond Probes	66
3.4 Data Calibration	66

4	Application of SSRM for Technology Development	73
4.1	Photovoltaic	73
4.1.1	Laser Doped Selective Emitter	74
4.1.2	Other Selective Emitter Concepts	78
4.2	Integrated Silicon Devices	79
4.2.1	Resist Lift Off	79
4.2.2	Gate Depletion	84
4.3	Power Devices	100
4.3.1	Super Junction MOSFET	101
4.3.2	Silicon Carbide Power Devices	106
5	Active Device Characterization by SSRM	113
5.1	Motivation	114
5.1.1	Dynamic Voltage	114
5.1.2	Active Devices	115
5.2	Test Devices	117
5.2.1	Sample Preparation	118
5.2.2	Influence of Preparation on IV-characteristics	120
5.3	Existing Methods for Active Device Characterization	122
5.3.1	Standard SSRM	122
5.3.2	Lock-in Amplifier based SDSRM	126
5.3.3	Scanning Voltage Microscopy	133
5.4	Scanning Dynamic Voltage Spreading Resistance Microscopy	138
5.4.1	Measurement Principle	138
5.4.2	Experimental Setup	140
5.4.3	Results	144
5.4.4	Summary	148
6	Summary and Outlook	149
6.1	General Summary	149
6.2	Outlook	150
	Bibliography	153
	Scientific contributions	171